

Notice of References CitedApplication/Control No.
10/019,540Applicant(s)/Patent Under Reexam
TakashiExaminer
Savitri MulpuriArt Unit
2812

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U.S. PATENT DOCUMENTS

	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Name	Classification ²	
A	4,939,571	7/1990	Nishizawa et al	----	----
B	6,407,435	6/2002	Ma et al	----	----
C	5,094,966	3/1992	Yamazaki	----	----
D	6,303,473	10/2001	Hefferman et al	----	----
E	2002/0098658 A	7/2002	Kolodzey et al	----	----
F	2003/0030078 A	2/2003	Manfra et al	----	----
G	6,296,956	10/2001	Hunter	----	----
H	6,391,748	5/2002	Temkin et al	----	----
I	2002/0175327 A	11/2002	Klee et al	----	----
J	2002/0090773 A	7/2002	Bojarczuk et al	----	----
K					
L					
M					

FOREIGN PATENT DOCUMENTS

	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Country	Name	Classification ²	
N						
O						
P						
Q						
R						
S						
T						

NON-PATENT DOCUMENTS

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Nikishin et al, "High-quality AlN grown on Si(111) by gas-source molecular -beam epitaxy with ammonia.", Appl Phys Letts Vol 75, number 4
V	
W	
X	

^{*} A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).¹ Dates in MM-YYYY format are publication dates.² Classifications may be U.S. or foreign.